


SANYO Semiconductors

DATA SHEET

2SK4100LS — N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- Adoption of high reliability HVP process.
- Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		650	V
Gate-to-Source Voltage	V _{GSS}		±30	V
Drain Current (DC)	I _{DC} *1	Limited only by maximum temperature	6	A
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	5.6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	24	A
Allowable Power Dissipation	P _D		2.0	W
		Tc=25°C (SANYO's ideal heat dissipation condition)*3	33	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	E _{AS}		105	mJ
Avalanche Current *5	I _{AV}		6	A

*1 Shows chip capability

*2 Package limited

*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

*4 V_{DD}=99V, L=5mH, I_{AV}=6A

*5 L≤5mH, single pulse

Marking : K4100

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2SK4100LS

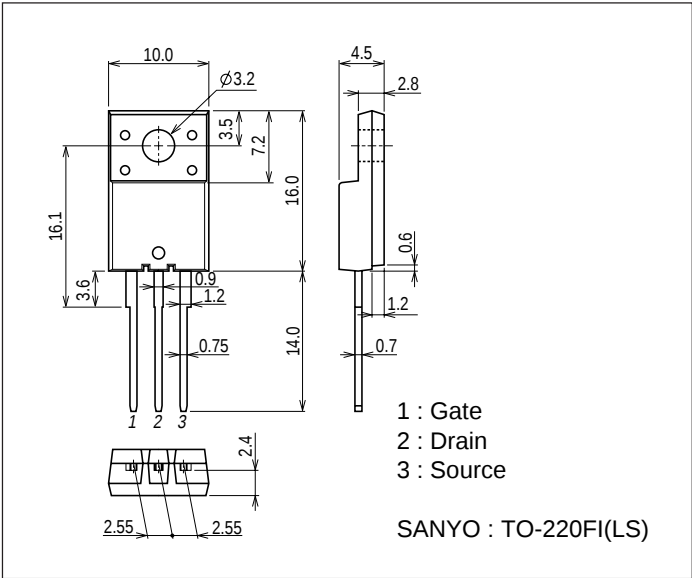
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0V$	650			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=520V, V_{GS}=0V$			100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$			± 100	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	3		5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=3A$	2	4		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=3A, V_{GS}=10V$		1.05	1.35	Ω
Input Capacitance	C_{iss}	$V_{DS}=30V, f=1MHz$		600		pF
Output Capacitance	C_{oss}	$V_{DS}=30V, f=1MHz$		110		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=30V, f=1MHz$		24		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		18		ns
Rise Time	t_r	See specified Test Circuit.		41		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		78		ns
Fall Time	t_f	See specified Test Circuit.		28		ns
Total Gate Charge	Q_g	$V_{DS}=200V, V_{GS}=10V, I_D=6A$		23		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=200V, V_{GS}=10V, I_D=6A$		4.5		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=200V, V_{GS}=10V, I_D=6A$		13		nC
Diode Forward Voltage	V_{SD}	$I_S=6A, V_{GS}=0V$		0.9	1.2	V

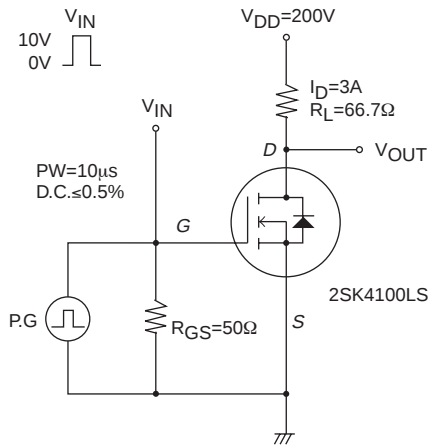
Package Dimensions

unit : mm (typ)

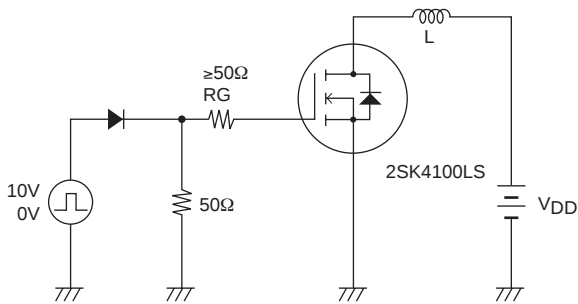
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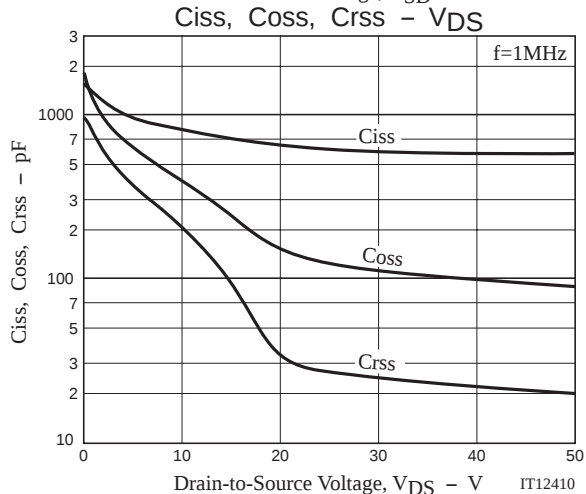
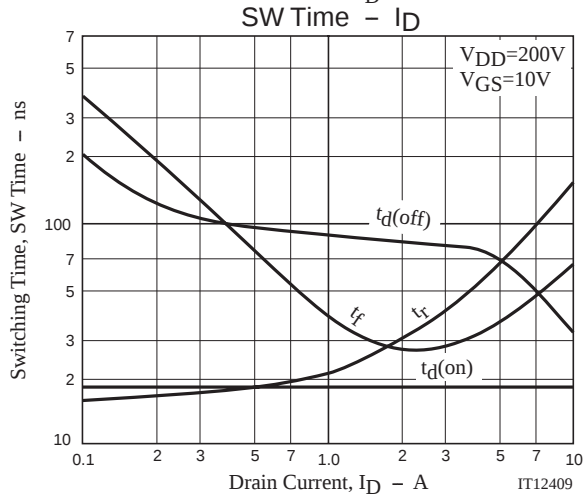
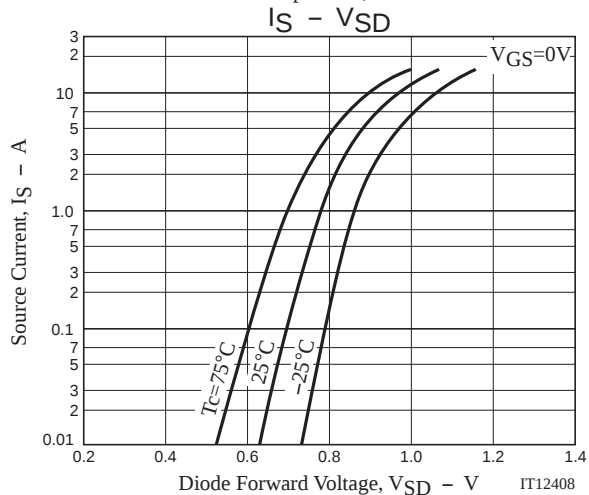
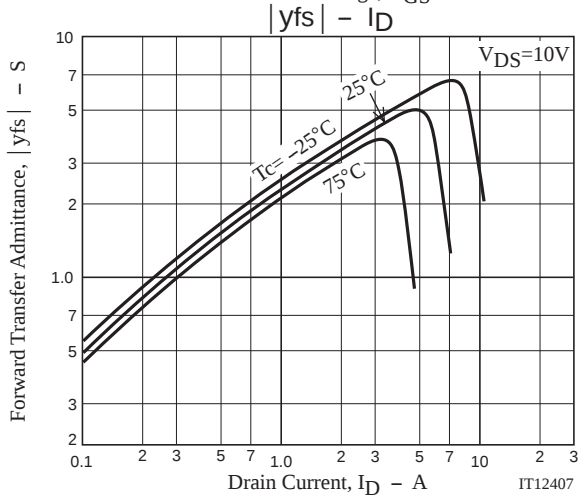
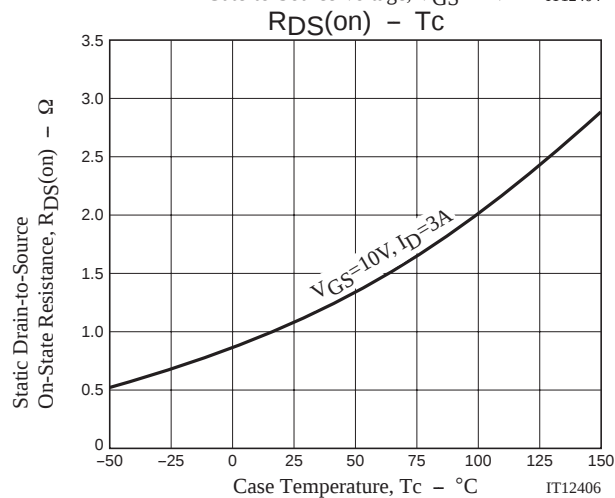
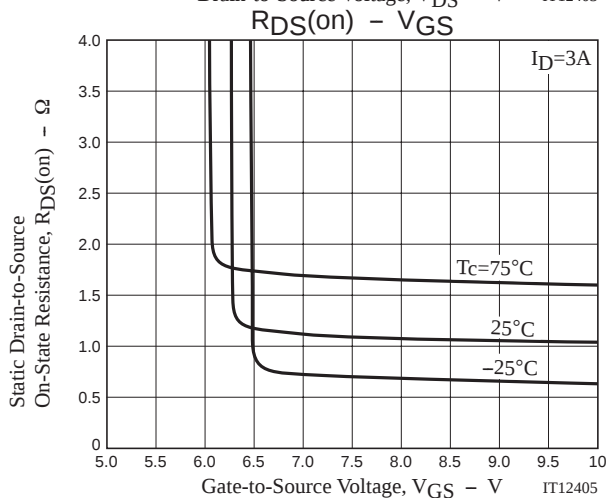
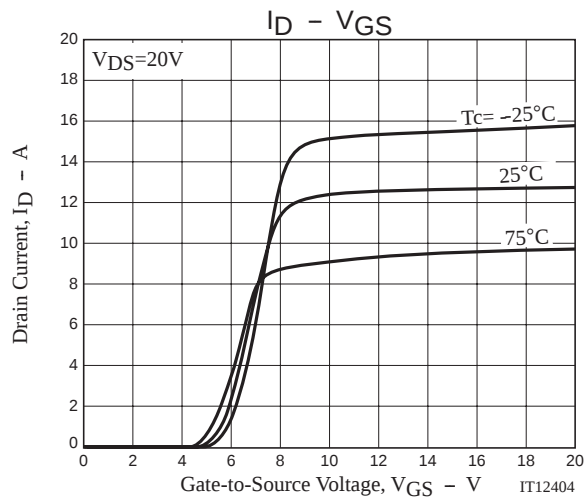
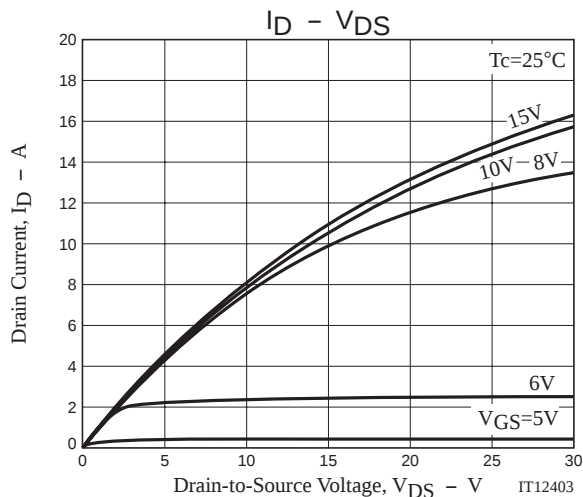
Switching Time Test Circuit



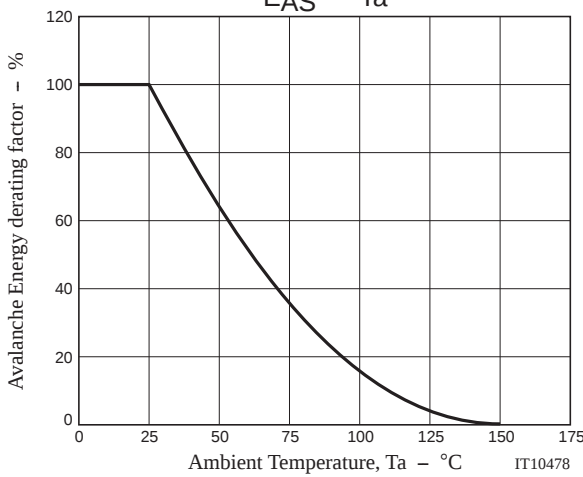
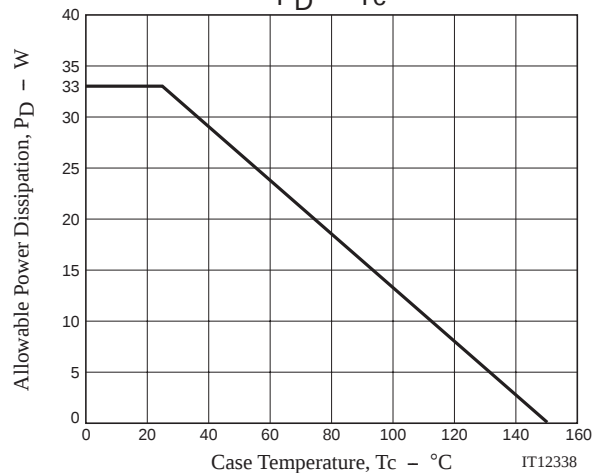
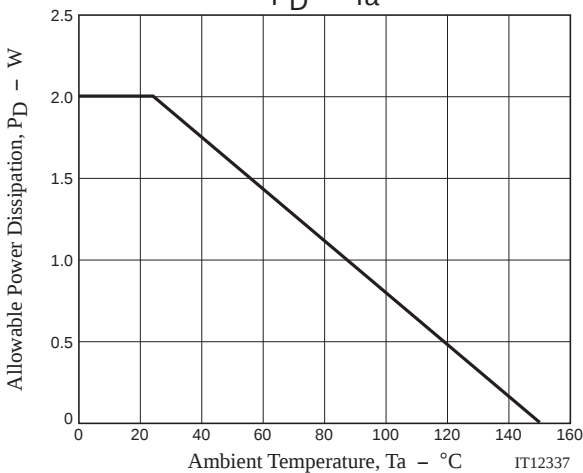
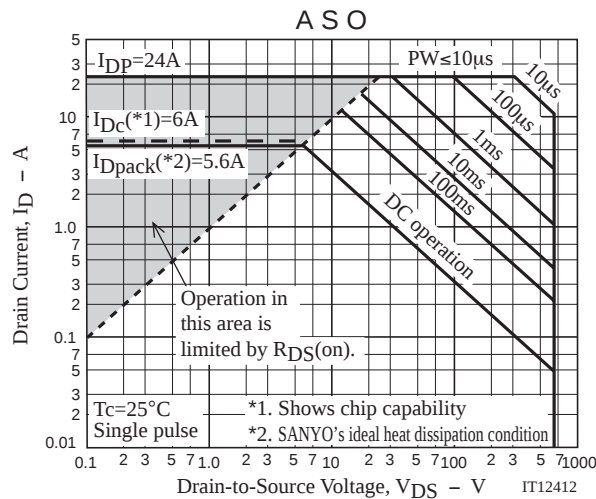
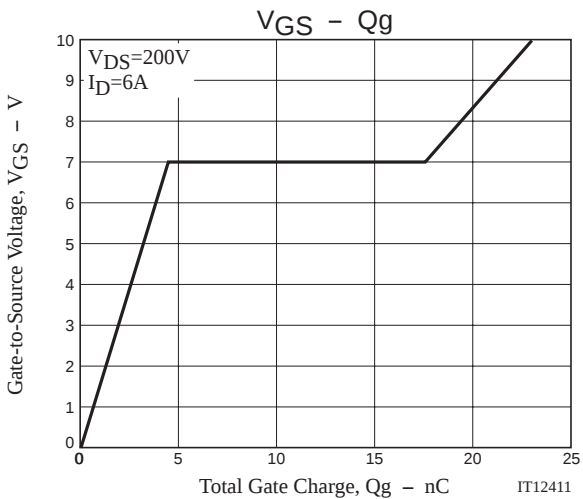
Avalanche Resistance Test Circuit



2SK4100LS



2SK4100LS



Note on usage : Since the 2SK4100LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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